

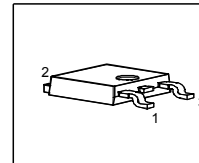
Cool MOS™ Power Transistor

Feature

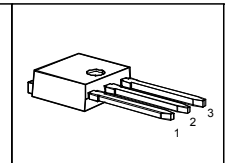
- New revolutionary high voltage technology
- Ultra low gate charge
- Periodic avalanche rated
- Extreme dv/dt rated
- Ultra low effective capacitances
- Improved transconductance

| | | |
|--------------|-----|----------|
| V_{DS} | 600 | V |
| $R_{DS(on)}$ | 1.4 | Ω |
| I_D | 3.2 | A |

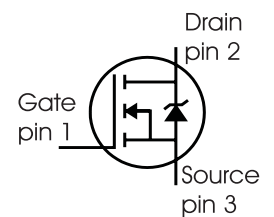
P-TO252.



P-TO251.



| Type | Package | Ordering Code | Marking |
|------------|----------|---------------|---------|
| SPU03N60S5 | P-TO251. | Q67040-S4227 | 03N60S5 |
| SPD03N60S5 | P-TO252. | Q67040-S4187 | 03N60S5 |



Maximum Ratings

| Parameter | Symbol | Value | Unit |
|---|---------------------|-------------|------------------|
| Continuous drain current $T_C = 25\text{ }^\circ\text{C}$ $T_C = 100\text{ }^\circ\text{C}$ | I_D | 3.2 2 | A |
| Pulsed drain current, t_p limited by T_{jmax} | $I_{D\text{ puls}}$ | 5.7 | |
| Avalanche energy, single pulse $I_D = 2.4\text{ A}$, $V_{DD} = 50\text{ V}$ | E_{AS} | 100 | mJ |
| Avalanche energy, repetitive t_{AR} limited by T_{jmax} ¹ $I_D = 3.2\text{ A}$, $V_{DD} = 50\text{ V}$ | E_{AR} | 0.2 | |
| Avalanche current, repetitive t_{AR} limited by T_{jmax} | I_{AR} | 3.2 | A |
| Gate source voltage | V_{GS} | ± 20 | V |
| Gate source voltage AC ($f > 1\text{ Hz}$) | V_{GS} | ± 30 | |
| Power dissipation, $T_C = 25\text{ }^\circ\text{C}$ | P_{tot} | 38 | W |
| Operating and storage temperature | T_j, T_{stg} | -55... +150 | $^\circ\text{C}$ |

Maximum Ratings

| Parameter | Symbol | Value | Unit |
|--|---------|-------|------|
| Drain Source voltage slope $V_{DS} = 480\text{ V}$, $I_D = 3.2\text{ A}$, $T_j = 125\text{ °C}$ | dv/dt | 20 | V/ns |

Thermal Characteristics

| Parameter | Symbol | Values | | | Unit |
|---|------------|--------|------|----------|------|
| | | min. | typ. | max. | |
| Thermal resistance, junction - case | R_{thJC} | - | - | 3.3 | K/W |
| Thermal resistance, junction - ambient, leaded | R_{thJA} | - | - | 75 | |
| SMD version, device on PCB: @ min. footprint @ 6 cm ² cooling area ²⁾ | R_{thJA} | - | - | 75 50 | |
| Soldering temperature, 1.6 mm (0.063 in.) from case for 10s | T_{sold} | - | - | 260 | °C |

Electrical Characteristics, at $T_j=25\text{ °C}$ unless otherwise specified

| Parameter | Symbol | Conditions | Values | | | Unit |
|---|---------------|--|--------|-------------|----------|------|
| | | | min. | typ. | max. | |
| Drain-source breakdown voltage | $V_{(BR)DSS}$ | $V_{GS}=0\text{V}$, $I_D=0.25\text{mA}$ | 600 | - | - | V |
| Drain-Source avalanche breakdown voltage | $V_{(BR)DS}$ | $V_{GS}=0\text{V}$, $I_D=3.2\text{A}$ | - | 700 | - | |
| Gate threshold voltage | $V_{GS(th)}$ | $I_D=135\mu\text{A}$, $V_{GS}=V_{DS}$ | 3.5 | 4.5 | 5.5 | |
| Zero gate voltage drain current | I_{DSS} | $V_{DS}=600\text{V}$, $V_{GS}=0\text{V}$, $T_j=25\text{ °C}$, $T_j=150\text{ °C}$ | - - | 0.5 - | 1 70 | μA |
| Gate-source leakage current | I_{GSS} | $V_{GS}=20\text{V}$, $V_{DS}=0\text{V}$ | - | - | 100 | nA |
| Drain-source on-state resistance | $R_{DS(on)}$ | $V_{GS}=10\text{V}$, $I_D=2\text{A}$, $T_j=25\text{ °C}$ $T_j=150\text{ °C}$ | - - | 1.26 3.4 | 1.4 - | Ω |

Electrical Characteristics , at $T_j = 25\text{ }^\circ\text{C}$, unless otherwise specified

| Parameter | Symbol | Conditions | Values | | | Unit |
|------------------------------|--------------|--|--------|------|------|------|
| | | | min. | typ. | max. | |
| Characteristics | | | | | | |
| Transconductance | g_{fs} | $V_{DS} \geq 2 \cdot I_D \cdot R_{DS(on)max}$, $I_D = 2\text{A}$ | - | 1.8 | - | S |
| Input capacitance | C_{iss} | $V_{GS} = 0\text{V}$, $V_{DS} = 25\text{V}$, $f = 1\text{MHz}$ | - | 420 | - | pF |
| Output capacitance | C_{oss} | | - | 150 | - | |
| Reverse transfer capacitance | C_{rss} | | - | 3.6 | - | |
| Turn-on delay time | $t_{d(on)}$ | $V_{DD} = 350\text{V}$, $V_{GS} = 0/10\text{V}$, $I_D = 3.2\text{A}$, $R_G = 20\Omega$ | - | 35 | - | ns |
| Rise time | t_r | | - | 25 | - | |
| Turn-off delay time | $t_{d(off)}$ | | - | 40 | - | |
| Fall time | t_f | | - | 15 | 22.5 | |

Gate Charge Characteristics

| | | | | | | |
|-----------------------|-----------------|---|---|------|----|----|
| Gate to source charge | Q_{gs} | $V_{DD} = 350\text{V}$, $I_D = 3.2\text{A}$ | - | 3.5 | - | nC |
| Gate to drain charge | Q_{gd} | | - | 7 | - | |
| Gate charge total | Q_g | $V_{DD} = 350\text{V}$, $I_D = 3.2\text{A}$, $V_{GS} = 0\text{ to }10\text{V}$ | - | 12.4 | 16 | |
| Gate plateau voltage | $V_{(plateau)}$ | $V_{DD} = 350\text{V}$, $I_D = 3.2\text{A}$ | - | 8 | - | V |

¹ Repetitive avalanche causes additional power losses that can be calculated as $P_{AV} = E_{AR} \cdot f$.

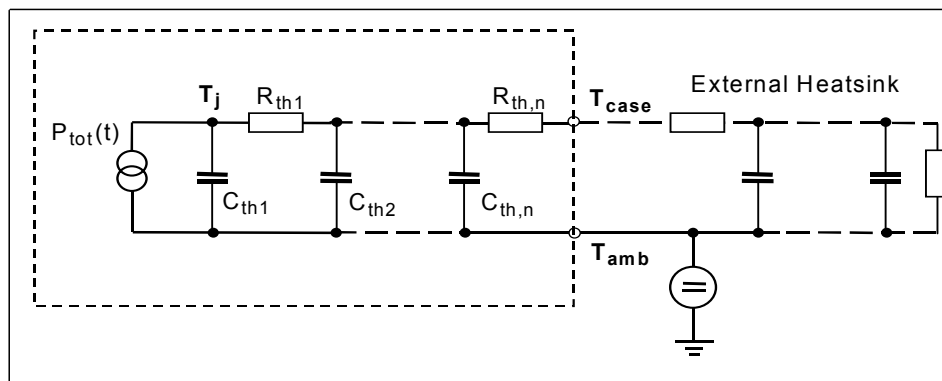
² Device on 40mm*40mm*1.5mm epoxy PCB FR4 with 6cm² (one layer, 70 μm thick) copper area for drain connection. PCB is vertical without blown air.

Electrical Characteristics, at $T_j = 25\text{ }^\circ\text{C}$, unless otherwise specified

| Parameter | Symbol | Conditions | Values | | | Unit |
|--|----------|-----------------------------------|--------|------|------|---------------|
| | | | min. | typ. | max. | |
| Inverse diode continuous forward current | I_S | $T_C=25^\circ\text{C}$ | - | - | 3.2 | A |
| Inverse diode direct current, pulsed | I_{SM} | | - | - | 5.7 | |
| Inverse diode forward voltage | V_{SD} | $V_{GS}=0\text{V}, I_F=I_S$ | - | 1 | 1.2 | V |
| Reverse recovery time | t_{rr} | $V_R=350\text{V}, I_F=I_S,$ | - | 1000 | 1700 | ns |
| Reverse recovery charge | Q_{rr} | $di_F/dt=100\text{A}/\mu\text{s}$ | - | 2.3 | - | μC |

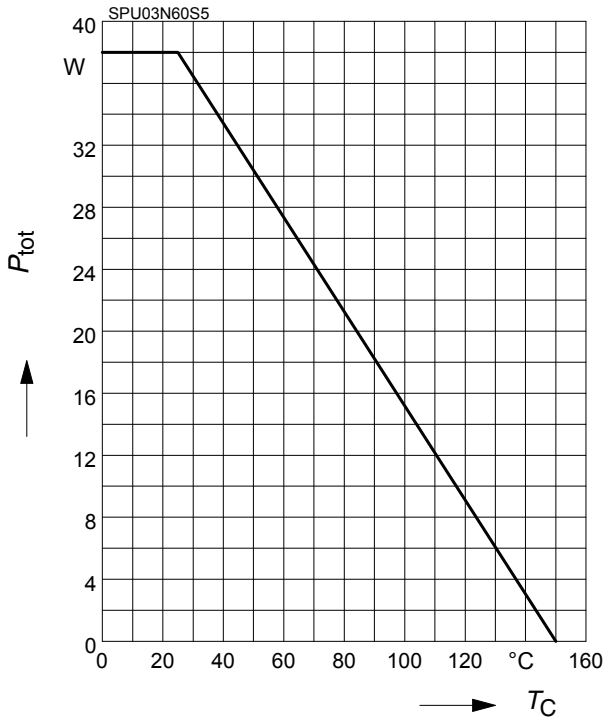
Typical Transient Thermal Characteristics

| Symbol | Value | Unit | Symbol | Value | Unit |
|--------------------|-------|------|---------------------|------------|------|
| | typ. | | | typ. | |
| Thermal resistance | | | Thermal capacitance | | |
| R_{th1} | 0.054 | K/W | C_{th1} | 0.00005232 | Ws/K |
| R_{th2} | 0.103 | | C_{th2} | 0.0002034 | |
| R_{th3} | 0.178 | | C_{th3} | 0.0002963 | |
| R_{th4} | 0.757 | | C_{th4} | 0.0009103 | |
| R_{th5} | 0.682 | | C_{th5} | 0.002084 | |
| R_{th6} | 0.202 | | C_{th6} | 0.024 | |



1 Power dissipation

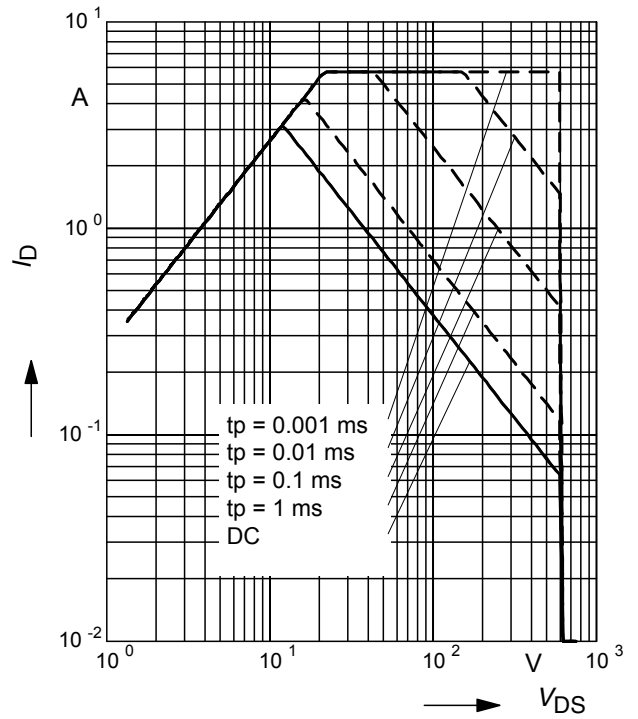
$$P_{tot} = f(T_C)$$



2 Safe operating area

$$I_D = f(V_{DS})$$

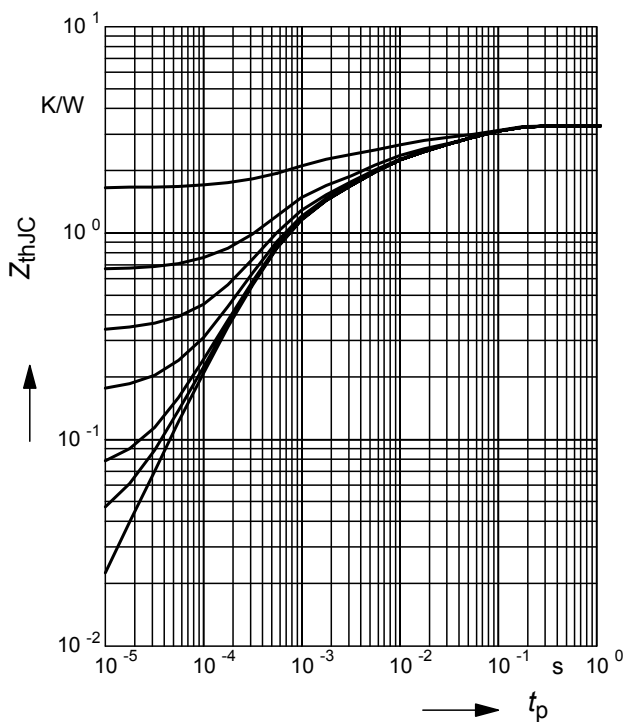
parameter : $D = 0$, $T_C = 25^\circ\text{C}$



3 Transient thermal impedance

$$Z_{thJC} = f(t_p)$$

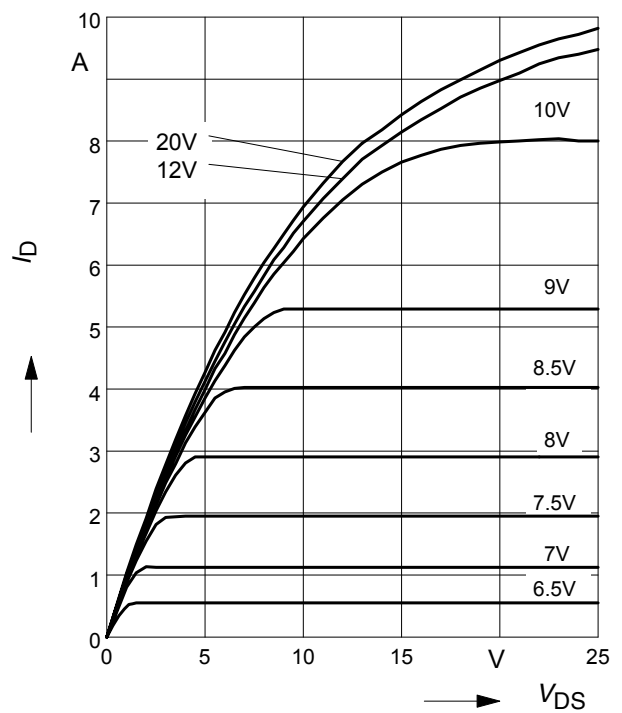
parameter: $D = t_p/T$



4 Typ. output characteristic

$$I_D = f(V_{DS}); T_j = 25^\circ\text{C}$$

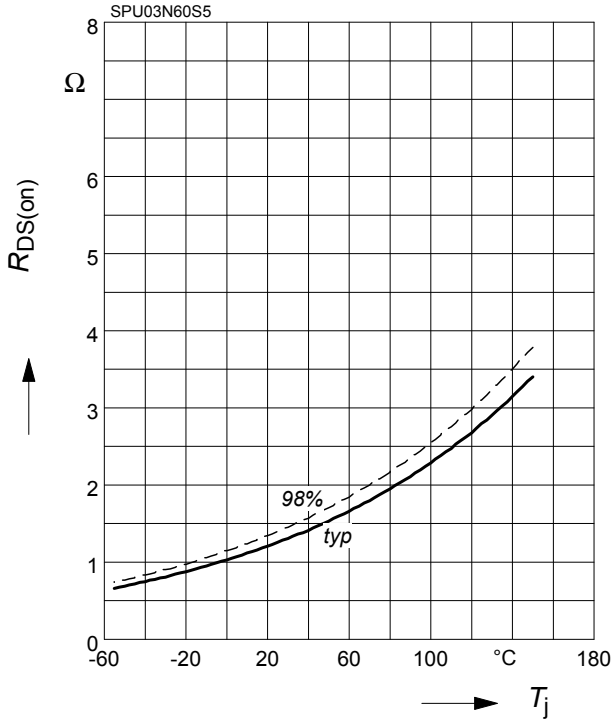
parameter: $t_p = 10 \mu\text{s}$, V_{GS}



5 Drain-source on-state resistance

$$R_{DS(on)} = f(T_j)$$

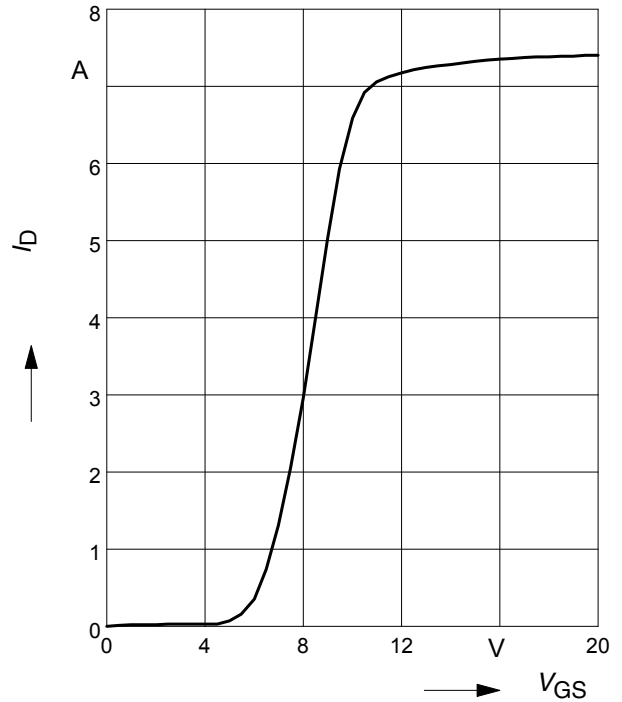
parameter: $I_D = 2\text{ A}$, $V_{GS} = 10\text{ V}$



6 Typ. transfer characteristics

$$I_D = f(V_{GS}); V_{DS} \geq 2 \times I_D \times R_{DS(on)max}$$

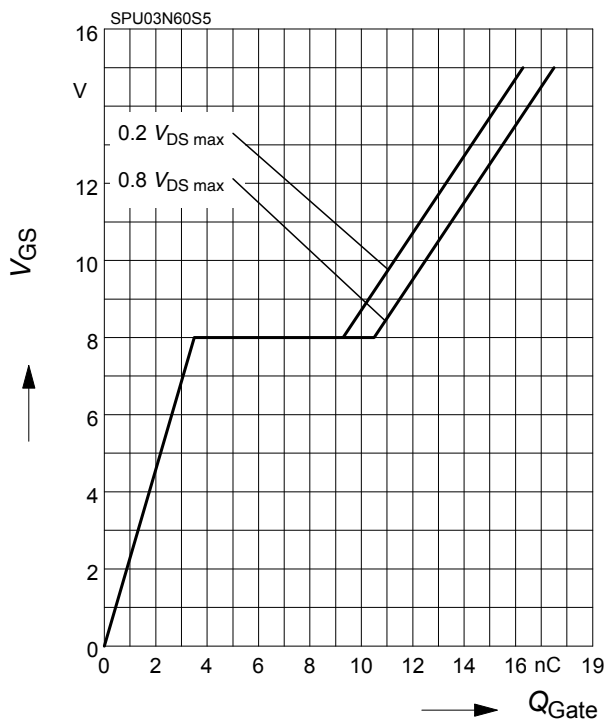
parameter: $t_p = 10\ \mu\text{s}$



7 Typ. gate charge

$$V_{GS} = f(Q_{Gate})$$

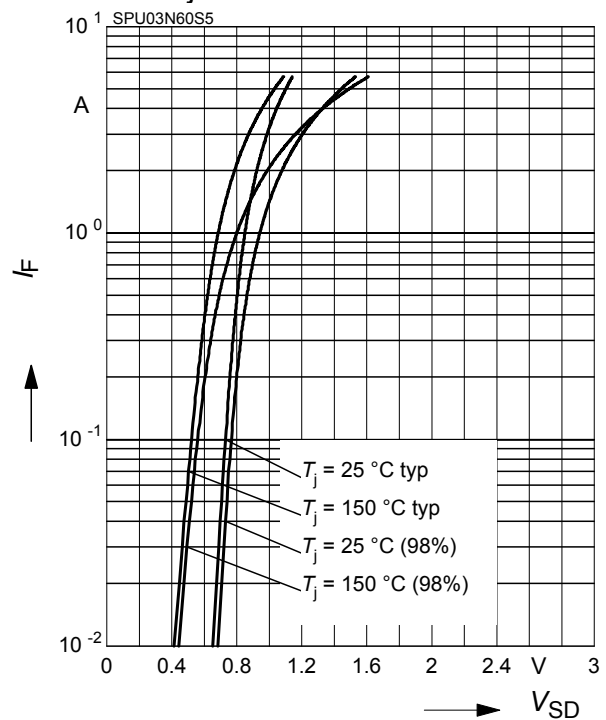
parameter: $I_D = 3.2\text{ A pulsed}$



8 Forward characteristics of body diode

$$I_F = f(V_{SD})$$

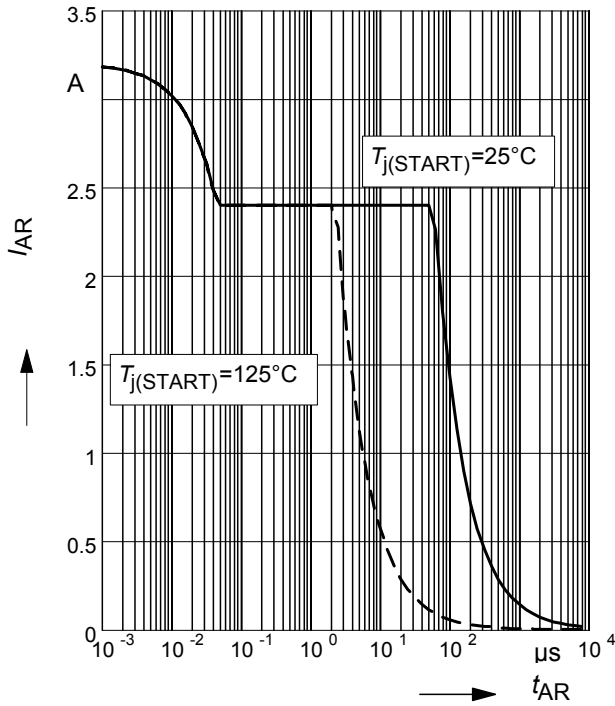
parameter: T_j , $t_p = 10\ \mu\text{s}$



9 Avalanche SOA

$I_{AR} = f(t_{AR})$

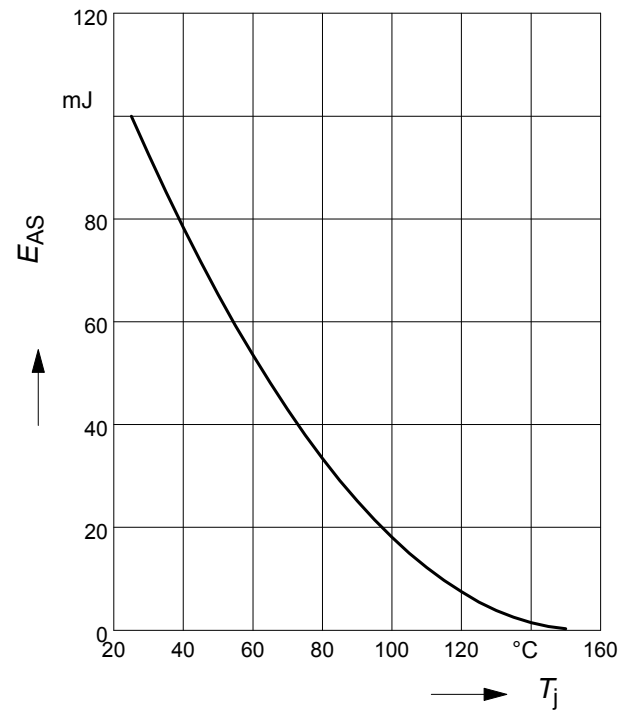
par.: $T_j \leq 150\text{ }^\circ\text{C}$



10 Avalanche energy

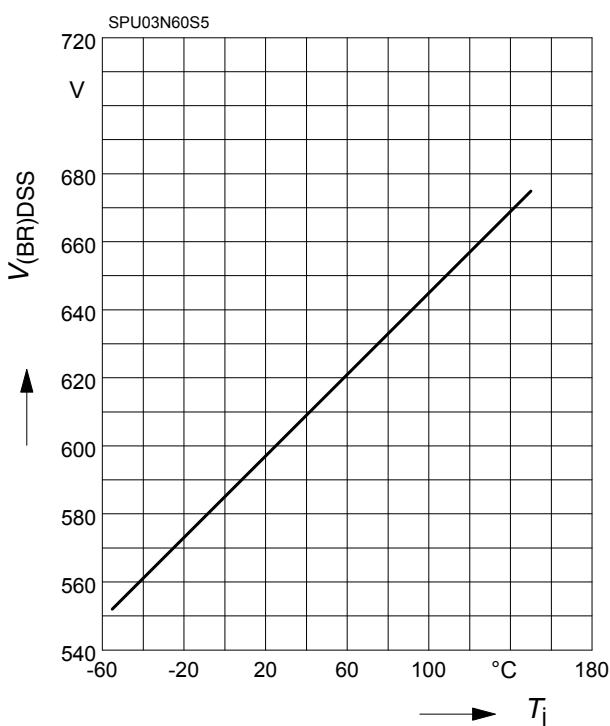
$E_{AS} = f(T_j)$

par.: $I_D = 2.4\text{ A}$, $V_{DD} = 50\text{ V}$



11 Drain-source breakdown voltage

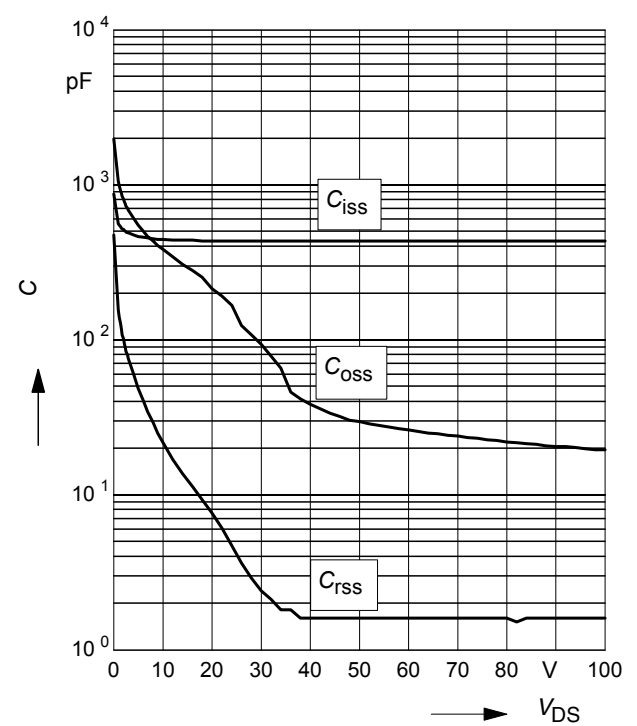
$V_{(BR)DSS} = f(T_j)$



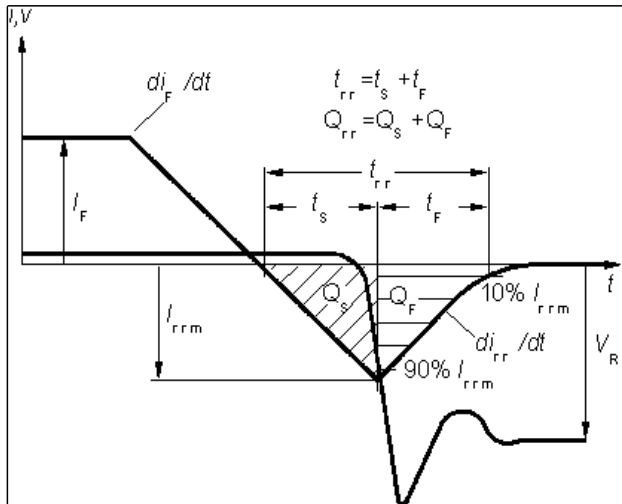
12 Typ. capacitances

$C = f(V_{DS})$

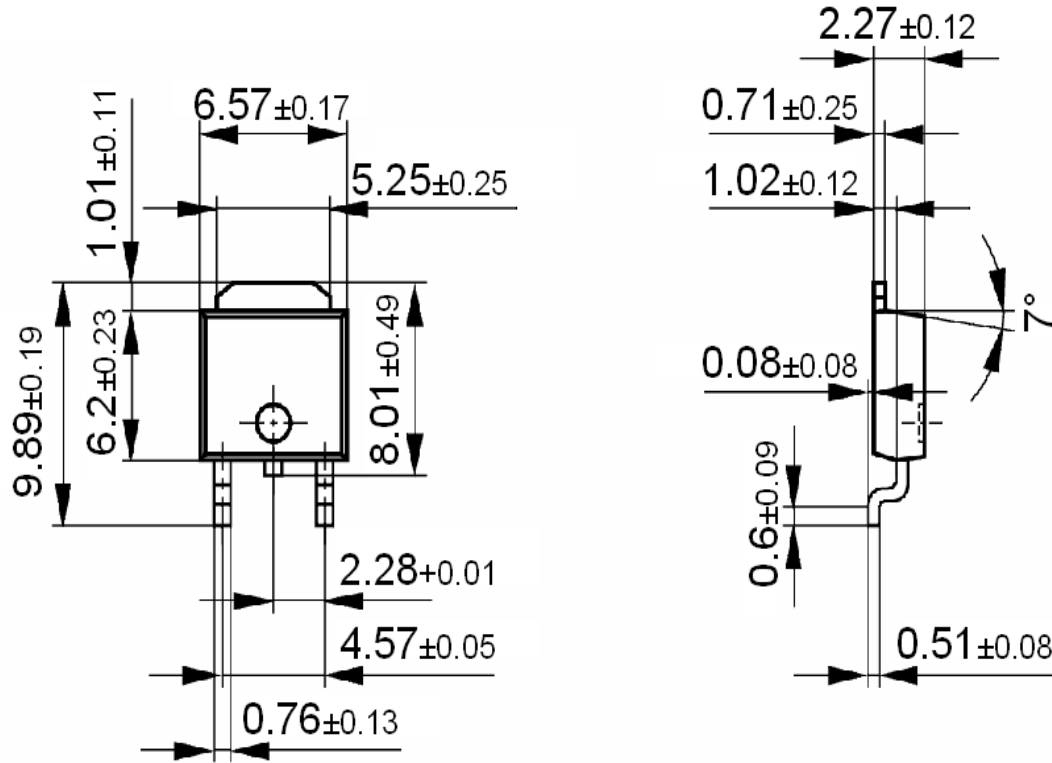
parameter: $V_{GS} = 0\text{ V}$, $f = 1\text{ MHz}$



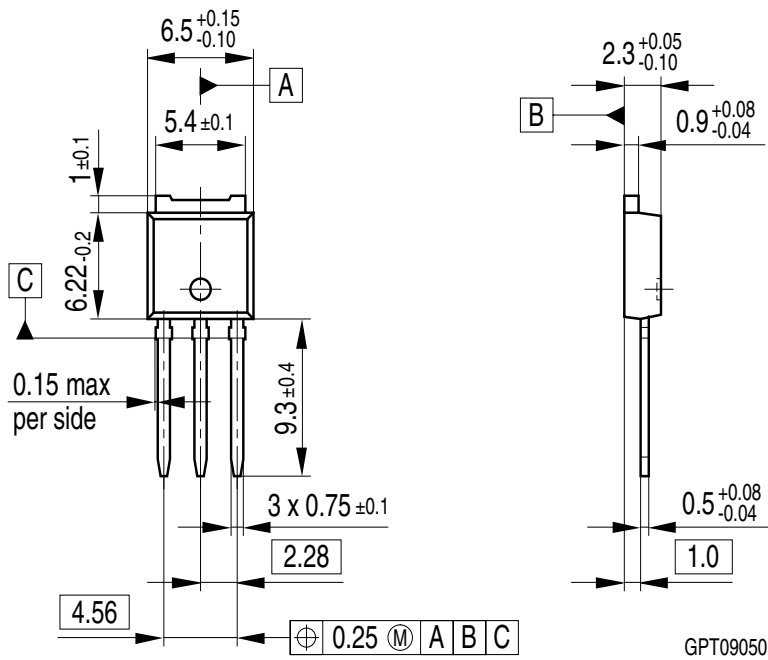
Definition of diodes switching characteristics



P-TO-252-3-1 (D-PAK)



P-TO-251-3-1 (I-PAK)



All metal surfaces tin plated, except area of cut.

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